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INSTRUCTION BOOK

RECEIVER, RADIO AN/GRR-23 and AN/GRR-24

VOLUME 2

EQUIPMENT CONTRACTOR INTERNATIONAL TELEPHONE AND TELEGRAPH CORPORATION FORT WAYNE, INDIANA F04606-74-C-0990 AND F34601-68-C-4219

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Item Desig.	Item Name	General Theory Page No.	Detailed Theory Page No.	Schematic Page No.
1	Receiver, Radio, UHF, AN/GRR-24	11-83	11-95	11-94
2	Receiver, Radio, VHF, AN/GRR-23	11-79	11-91	11-90
1A1 or 2A1 (Deleted) 1A1 or 2A1 (Deleted)				
1A1(M) or 2A1(M)	Oscillator-Multiplier (8009546G1)		11-23	11-22
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1PS1 or 2PS1	Power Supply		11-75	11-74

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CIRCUIT IDENTIFIER CODES

CATEGO	RY DEFINITIO	N	CATEGORY	DE	FINITION		
C	Composite circuit (one functionalized); compose entities containing one of functional entities (N, C given in this list are prec	site function for more of (), V, or X)	onal the	Q Circuits containing one or more linear elements which may be e active or passive; functional en containing transistors are prece by Q.			
L	Used in logic diagrams of lowest level of functional logic circuits.			Circuits containing one or more non linear elements which may be either active or passive; functional entities containing vacuum tubes are precede			
М	Microwave components attenuators, etc.).	(duplexers	S, .	by V.			
N	Linear networks; function containing several linear (resistors, capacitors, etc a network or containing element used as network by N.	componer c.) arrange a single	nts d in	linear elements active or passiv	ining one or more non- s which may be either ve; functional entities niconductor diodes are		
CODE	DEFINITION	CODE	DEFINITION	CODE	DEFINITION		
AGC	Automatic gain control	FQD	Frequency quadrupler	ТВ	Terminal board		
ALC	Audio level control	GAT	Gating	TFR	Transformer		
AMP	Amplifier	HTR	Heater	TR	Transmit-receive		
ANC	Antenna coupler	LA	Lamp (indicating)	VD	Voltage divider		
AT	Attenuator	LIM	Limiter, limiting	VDR	Voltage doubler		
AUA	Audio amplifier	LO	Local oscillator	VR	Voltage regulator		
AUO	Audio oscillator	LS	Level shifter				
BCG	Battery charging	LVC	Level control circuit				
BUF	Buffer	MIC	Microphone				
CA	Control amplifier	MIX	Mixer				
CGT	Compression gate	MMV	Monostable multivibrator	г			
CMP	Compression	MOD	Modulator				
CMR	Comparator	MON	Monitor				
CTR	Counter	MTC	Matches				
CPR	Clipper	MTG OSC	Matching				
DET	Detector	USC	Oscillator				
DFA	Differential amplifier	PS	Pouros au-alu				
DG	Diode gate	RCT	Power supply Rectifier				
DL	Delay line	REG	Regulator				
EF	Emitter follower	RFA	-	-			
FDR	Frequency doubler	RLY	Radio frequency amplifie Relay	Γ.			
FDV	Frequency divider	SW	Switch				
FL	Filter	11	Switch				

.



EXPLANATION OF SPECIAL SYMBOLS



EXPLANATION OF SHADED AREAS

SECTION 11

DIAGRAMS

<u>11.1 INTRODUCTION</u>.- This section contains the schematic diagrams for the vhf and uhf receivers and their subassemblies. The schematics of the individual integrated circuits used in the receiver are also included. Shaded blocked diagrams and texts and blocked schematic diagrams and texts complete this section. The interconnecting wiring between subassemblies and between subassemblies and external connections is listed in table 11-1.

11.2 USE OF SUBASSEMBLY SCHEMATIC DIAGRAMS.- The subassembly schematics in this section are intended chiefly as maintenance tools together with the assembly drawings and photographs in section 10. Test points (TP) and measurement points (MP) are accentuated and the d.c. voltages at these points are listed on each schematic.

<u>11.3 SHADED BLOCKED DIAGRAMS AND TEXTS</u>. Figures 11-30 through 11-33 present a secondlevel functional description of the vhf and uhf receivers in blocked diagrams and companion blocked texts. Figures 11-34 and 11-35 present a functional block diagram and companion text for the optional oscillator-synthesizer module that may be used in either receiver unit.

<u>11.4 SHADED BLOCKED SCHEMATIC DIAGRAMS AND TEXTS</u>. Figures 11-36 through 11-39 present the shaded functionally oriented blocked schematic diagrams and companion text discussions of the uhf and vhf receivers, respectively. It should be noted in these schematics that the mixer/multiplier (A2) is shown only in the G2 configuration, which is only slightly different from the G1 configuration. Figures 11-40 and 11-41 present the shaded functionally oriented blocked schematic dia-

 gram and companion text of the oscillator-multiplier and the optional oscillator-synthesizer module that may be used in either receiver unit.

Table 11-1. Receiver Wire List

	From	n termina	1	То	terminal					Approx.		
Wire number	Connector	Pin	Conn Iug	Connector	Pin	Conn lug	Туре	Gauge	Color	length (inches)	Notes	Remarks
						8	-77-					
1	J15	16	2	E4		· 4	E	22	- 0	9		
2	J15	14	2	J3	2	DF	E	22	7	115		
3	J15	13	2	J3	3	DF	E	22	2	11¾		
4	J15	12	2	J4	13	DF	Е	22	4	13½		
5	J15	11	2	J4	8	DF	Ε	22	9	13¾		
6	J15	10	2	J9	8	DF	Y	22	5	15%	1	
7	J15	9	2	J6	5	DF	E	22	6	15%		
8	J15	8	2	J7	7	DF	Е	22	95	13		
9	J15	6	2	J6	6	DF	Е	22	1	16¼		
10	J15	4	2	J 7	11	DF	Е	22	96	13¾		
11	J15	3	2	J8	5	DF	Е	22	93	16		
12	J15	2	2	J4	7	DF	E	22	90	16		
13	J15	1	2	J5	8	DF	E	22	· 8	185		
14	J14	Т	4	J5	13	DF	Е	22	96	16½		
15	J14	R	4	J5	12	DF	Е	22	95	16%		
16	S1	1	4	· J4	15	DF	Е	22	91	5		
17	S1	2	4	R1	1	2	E	22	9	4		
18 ·	S1	3	4	J4	9	DF	E	22	3	15		
19 `	R1	2	4	J4	10	DF	Е	22	7	14½		•
20	R1	3	2	J4	11	DF	Е	22	8	14½		
21	R3	1	2	R2	1	2	E	22	1	4		
22	R3	1	2	J4	5	DF	Ε	22	1	15		
23	R3	3	2	R2	3	2	E	20	0	4		
24	R3	3	2	E4		4	Е	20	0	10¾		
25	R3	2	2]5	7	DF	Е	22	7	17		
26	R2	2	2	J5	5	DF	E	22	90	16¾		
27	J3	1	DF	E3		4	Е	20	0	4¼		
28	J3	4	DF	J6	3	DF	Е	22	2	9		
29	J3	6	DF	J7	3	DF	Е	22	2	6½		
30	J3	8	DF	J 8	3	DF	E	20	2	81/2		
31	J3	9	DF	J9	3	DF	E	20	2	9		

TI 6620.2A

Wire		ı termin	Conn		terminal	Conn				Approx. length	Υ.		
number	Connector	Pin	lug	Connector	Pin	lug	Туре	Gauge	Color	(inches)	Notes	Remarks	
32	J3	10	DF	J4	3	DF	E	20	2	81⁄2			
33	J3	11	DF	J5	3	DF	E	20	2	10			
34]3	12	DF	J6	2	DF	E	22	7	8¾			
35	J4	1	DF	E3		4	Е	20	0	4			
37	J4	6	DF	J5	15	DF	E	22	6	8¾			
38	J4	14	DF	E6		2	E	22	5	6			
39	J5	1	DF	E2		4	E	20	0	4¼			
40	J5	9	DF	C2	1	25	E	22	4	11¼	2		
41	J5	11	DF	· C3	1	2S	E	22	3	11¼	2		
42	J5	10	DF	C4	1	2S	Ε	22	9	11¼	2		
43	J7	1	ÐF	E7		4	E	20	0	71⁄2			
44	J7	5	DF	E6		2	Е	22	5	4			
45	J6	1	DF	E7		4	E	20	0	3			
46	J8	1	DF	E7		4	E	20	0	7 1⁄2			
47	J9	9	DF	E6		2	E	22	5	10			
48	.s J9	1	DF	E5		4	E	20	0	5			
49	J 9	5	DF	C5		2S	Y	22	6	10	3&2		
50	J9	7	DF	J4	12	DF	E	22	95	7 <u>3</u> 4			
53	C1	1	28	E6		2	Е	22	5	14	2		
54	C8	1	2S	XF3	1	4	Е	22	6	2334	2		
55	XF3	2	4	S2	3	4	E	22	7	91/2	÷		
56	S2	7	4	J3	7	DF	Е	22	6	18			
60	J3	5	DF	J6	4	DF	E	22	92	7			
61 -	C6	1	2 S	XF1	1	4	R	20	8	221/2			, H H
62	C7	1	2S	SF2	1	4	R	20	98				σ
63	XF1	2	4	S2	1	4	R	20	1	11			62
64	XF2	2	4	S2	2	4	R	20	91				ö
65	Withdraw	n by A	F P 6500.	1 CHG Chap	, .								N
66	Withdraw												* 🎽
67	S2	5	4	J3	14	DF	R	20	8	81/2			
68	S2	6	4	J3	15	DF	R	20	98				

Table 11-1. Receiver Wire List (con.)

.

	Table 11-1. Receiver Wire List (con.)													
	Wire number	From Connector	n termin Pin	nal Conn lug	To Connector	terminal Pin	Conn lug	Туре	Gauge	Color	Approx. length (inches)	Notes	Remarks	F 6500.1 ap 391 1 : 6620.2:
*	69 70	E4 J15	13	2 2	XDS1 XDS1	1 2	2 2	E E	22 22	0 2	121/2 141/2			. CHG 413 ./18/90 A *

NOTES - CODE IDENTIFICATION

"Wire number" colum	n: Numbers 36, 51, 52, 57, 58, and 59 deleted.	"Color" column:	0 Black	6 Blue	
			1 Brown	7 Violet	
"Conn lug" columns:	DF denotes 502056-402 contact, female		2 Red	8 Gray	
2	S denotes sleeving, insulation		3 Orange	9 White	
	2 denotes 1/4" strip length		4 Yellow		
	4 denotes 1/2" strip length		5 Green		
"Type" column:E d	enotes 4590 wire	"Notes" column:	1 Solder shields of wire gates		
`Y d	enotes 4596 wire, shielded and jacketed			eeving, insulation	
R de	enotes 517875 wire, twisted pair		3 Solder shi	eld of wire 49 at E1 and E5	

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Figure 11-1. VHF/UHF Receiver Schematic



PIN ASSIGNMENT (TOP VIEW)



Figure 11-2. Fixed Resistor Network Integrated Circuit (509435-1)



PIN ASSIGNMENT (TOP VIEW)

POSITIVE LOGIC: Y = ABC



SCHEMATIC (EACH GATE)





PIN ASSIGNMENT (TOP VIEW)



SCHEMATIC (EACH GATE)







Figure 11-5. Operational Amplifier Integrated Circuit (SN52741L-00)

(



Figure 11-6. Operational Amplifier Integrated Circuit (LM101AH)







Figure 11-7. Switching Regulator Integrated Circuit (PIC600)



TERMINAL ARRANGEMENT (BOTTOM VIEW)



Figure 11-8. Transistor Array Integrated Circuit (CA3118T)

(5) Q_A

.<u>(9)</u> 0₈

(<u>(2)</u> 0_C

-<u>(1</u>2)_{QD}

Preset

>TOA

Clear

QB

'ск

7

Preset

, a_DF

CK



Figure 11-9. High-Speed Counter Integrated Circuit (SN54196J-00)









INPUTS					OUTPUTS	
PRESET	CLEAR	CLOCK	J	ĸ	0	0
L	H	x	X	х	н	L.
н	L	X	X	Х	L	н
L	L	X	X	X	Н.	Н•
н	Н	**	L	L	0 ₀	QO
н	Η	**	н	L	н	L
н	н	**	L	Н	L	N
н	н		H.	н	TOGG	LE
н	н	H.	X	X	_ QO	QO
			,,,,,,,,,			



X = IRRELEVANT

FUNCTION TABLE

*THIS CONFIGURATION IS NONSTABLE; IT WILL NOT PERSIST WHEN PRESET & CLEAR INPUTS RETURN TO THEIR IN-ACTIVE (HIGH) LEVEL. **TRANSITION FROM HIGH TO LOW LEVEL "TOGGLE" = EACH OUTPUT CHANGES TO THE COMPLEMENT OF ITS PREVIOUS LEVEL ON EACH ACTIVE TRANSITION (PULSE) OF THE CLOCK. "OO" = THE LEVEL OF Q BEFORE THE INDICATED INPUT CONDITIONS WERE ESTABLISHED.

FUNCTIONAL BLOCK DIAGRAM

Figure 11-11. Edge-Triggered J-K Flip Flop Integrated Circuit (SN54H102J-00)



A CLOCK H IS A CLOCK TRANSITION FROM A LOW TO A HIGH STATE







CIRCUIT SCHEMATIC 1/2 OF CIRCUIT SHOWN

RS TRUTH TABLE

R	S	Qn+1				
L	L	Qn				
L	Н	н				
Н	L	L				
н	н	N.D.				
N.D. = NOT DEFINED						

CLOCKED TRUTH TABLE $\begin{array}{c|c}
C & D & Q_{n+1} \\
\hline
L & 0 & Q_n \\
\hline
H & L & L \\
\hline
H & H & H \\
\hline
0 = DON'T CARE \\
C = C_E + C_C
\end{array}$

Figure 11-12. Dual Master-Slave (D-Type) Flip Flop Integrated Circuit (MC10531L)

- Vcc1

~ v_{EE}

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Figure 11-13. Crystal Oscillator A1 G1 (This figure deleted)

Figure 11-14. Crystal Oscillator A1 G2 (This figure deleted)



Figure 11-15. Oscillator-Multiplier A1(M)

AF P 6500.1 CHG 361 Chap 356 1/28/83 OSCILLATOR-MULTIPLIER A1(M)

The oscillator-multiplier module is directly interchangeable with the oscillator-synthesizer module. The oscillator-multiplier module utilizes a fundamental crystal. Frequency accuracy is determined by "pulling" the crystal. Tuning to the exact frequency is accomplished by monitoring the frequency with a counter or frequency meter connected to J1.

The oscillator-multiplier module consists of a crystal-controlled oscillator and multiplier stage, a buffer amplifier stage, and an output amplifier stage. The oscillator-multiplier requires a fundamental mode crystal operating in the frequency range of 11.25 MHz to 99.975 MHz. The output frequency from the module is 5 times the crystal frequency.

Oscillator stage Q1 is a modified Colpitts circuit. Crystal Y1 operates in an antiresonant mode. Paralleled capacitor combination, C2, C3, and C25, in series with the crystal, controls the frequency. Capacitor C25 is internally adjusted at the factory so that the desired oscillator frequency falls at the C3 adjustment range midpoint. Capacitors C4 and C5 form the feedback divider characteristic of the Colpitts configuration. Transistor Q1 is biased into conduction by voltage divider R3 and R4. The Q1 emitter return is R5. The Q1 collector circuit is tuned to the oscillator fifth harmonic by the resonant circuit L2-C10, C11. Capacitor C10 is the front panel tuning element. The Q1 d.c. input is regulated at 12 volts by VR1. Oscillator power supply isolation is by R1, R6, C6, and C7. The tuned circuit RF ground is through C8. Collector circuit current limiting is provided by R2. Resistance R7 is impedance isolation between the oscillator-multiplier tuned circuit and buffer bandpass filter L4-C15, C16, tuned to the crystal fifth harmonic.

Buffer amplifier Q2 is an emitter follower that minimizes shunt loading on the L4-C15, C16 filter preceding it, and drives the output amplifier stage following it. Capacitor C16 is the front panel tuning element. Voltage divider R9, R10 provides base bias for Q2. Resistor R11 is the emitter load.

Stage Q3 is the output RF amplifier of the oscillator-multiplier module. The signal is applied to the Q3 base by direct coupling from the buffer amplifier via parasitic suppression resistor R14. Resistors R15 and R16 provide emitter bias. The collector circuit is tuned by L3-C20, C21 to the crystal fifth harmonic. Capacitor C21 is the front panel tuning element: The output passes through attenuator network R18, R19, which buffers the output to the driven stage, and stabilizes the output impedance to approximately 50 ohms.

The signal is branched from the output stage via R17 into diode detector CR1 for metering the signal level for tuning purposes. RF filtering is provided by network L6, C23, and C24. Resistors R12 and R13 determine the scale factor of the external indicating meter.

An external signal generator can be used if desired. To do so, crystal Y1 is removed, disabling the oscillator, and 1-2 V rms is applied to J1 from the external signal generator. The signal generator must be set to the desired output frequency, i.e., 5 times the crystal frequency. Front panel tuning capacitors C16 and C21 are then adjusted for maximum output on the meter.





OSCILLATOR – SYNTHESIZER A1(S)

The oscillator-synthesizer generates selectable stable frequencies by a voltage-tuned oscillator. The selected oscillator output frequency is fed to a prescaler counter which divides the frequency by 4 and feeds it to a variable counter. The variable counter further divides the frequency by a ratio of 9,000 to 15,999 as determined by the settings of the frequency select thumbwheels. The division ratio of the counter is such that when the voltage-tuned oscillator is generating the correct frequency, the output of the variable counter is 1.5625 kHz. This output signal is fed to a phase detector and compared with a 1.5625 kHz reference signal. The 1.5625 kHz reference signal is derived from a precision crystal-controlled oscillator and a digital fixed-frequency divider counter. The phase difference between these two signals determines the d.c. voltage which controls the voltage-tuned oscillator is + 14 dBm ± 3 dBm.



Figure 11-17. Divider/Control A1A1(S)

11-28/11-27 (blank)

GTLS: UNLESS OTHERWISE SPECIFIED: 1. ALL RESISTANCE VALUES ARE IN OHMS, ±5%, 1/8 W 2. ALL CAPACITANCE VALUES ARE IN MICROFARADS, ±20%, 1000V

DIVIDER/CONTROL A1A1(S)

This board determines the output frequency. The board contains a prescaler (divide by 4) and a variable counter with its associated frequency selection switches. The RF sample from the RF generator board is fed through attenuator R15 and R16. C5 is a d.c. block which couples the RF to the base of amplifier Q4. This device places the RF at a d.c. level of about 3.2 volts (by virtue of bias resistors R17 and R18) which is the optimum input level for U8. U8 is an emitter-coupled logic dual-D flip-flop which is hooked up to divide the input RF signal (56.25 MHz to 99.9937 MHz) by 4. The output of U8 is fed to an emitter-coupled pair Q1 and Q2. This circuit amplifies the output of U8 and shifts the signal level to that of TTL (transistor-transistor logic). Q3 is used as a saturating switch which drives the first logic gate.

The variable counter number (divide by N) is essentially a chain of programmable counters constructed entirely with monolithic integrated circuits. The division ratio N ranges from 9,000 to 15,997 and is programmed by generating binary logic levels with the four-digit frequency selector thumbwheel switches. The first three switches are inverted "nines" complement binary coded decimal (bcd). Switch S4 is hexadecimal code which programs U5 (divide by 16). S1, S2, and S3 program U2, U3, and U4 respectively, which are divide by 10 counters. Assuming the thumbwheels are set to 99.9937, this means all switches are made placing a "low" on all the inputs, so the division ratio is 15,997. Thus the signal is coupled through the NAND gate (U7) following Q3 and into U5. This divides the input 24.9984375 MHz pulse train by 16. The output of U5 drives the input of U4 which divides by 10. This signal then drives U3, which drives U2, each of which divide by 10. When the counter reaches 99.9937 (by dial), or 15,997 pulses have been counted, the inputs to the U1 AND gates are all high, which drive a three-input AND gate in U6, causing it to change states. This resets U2, U3, U4, and U5, and causes a pulse out of pin 8 of U6 into a NAND gate of U7. This drives another NAND gate, whose output is shaped by C4 and R14 to drive another NAND gate, which is the output of the divider. These NAND gates are used to shape the output of U3 to a narrow pulse (approximately 10 μ s) which drives the phase comparator.

If the thumbwheels are set to numbers other than 99.9937, the inputs to the divider counters are made high through the switch. Z1 is a resistor network consisting of 15 each 4.7-kilohm pull-up resistors with one lead common to pin 16 (B+). No change will occur until the data strobe drops to a logic zero (Q of U6 upon full count). At that time the data on the inputs will be transferred to their associated counters and the count will take up from there on the next clock pulse. Under these conditions, the count required will be shortened by the amount of the preset inputs.





RF GENERATOR A1A2(S)

The RF generator provides the output signal of the synthesizer, as well as driving the divider control prescaler. The printed wiring board contains the oscillator, limit controls for the oscillator, a buffer amplifier, a final amplifier, and a voltage regulator. The oscillator is basically a voltage-tuned Hartley circuit, with tank L2, CR1, and CR2. CR1 and CR2 are voltage variable capacitors (varactor diodes) whose capacity is dependent on the amount of reverse voltage. This control voltage is obtained from the output of the phase comparator, and is coupled through R29 and R3, with C22 used as a bypass. Q1 is a high-frequency field-effect transistor, with R1, R2, R35. R36, and R37 providing bias and feedback. C2, C3, C7, C26, and C27 are all bypass capacitors, and C5 and C25 are blocking capacitors. L1 is an autotransformer and is used to couple the signal out to the buffer amplifier Q2, through R4, C4, and C28.

R10 is a d.c. feedback resistor, and R9 is the collector load. L3, C11, L4, and C12 are low-pass filter sections to reduce the second harmonic, with C8, C9, and C23 used as bypasses. L5 is an autotransformer and couples the signal into signal splitter L6. R11, R12, and R13 are used to attenuate the signal which goes back to the divider control. L7, C16, and R15 match the input impedance of Q3, the final amplifier. R18 is the d.c. feedback with R17 the collector load. L8, C17, L9, and C18 are two low-pass filter sections to reduce harmonics, with C10, C15, and C24 bypasses. L10 is an autotransformer which couples the signal to C19, a d.c. block. R19, R20, and R21 are used to attenuate the signal to provide isolation from loading effects of the synthesizer output. R22, CR3, C20, R23, C21, and R24 form an RF detector which indicates the presence of RF on the receiver front panel L0 test point.

U1 is a transistor array of two individual transistors and two transistors internally connected as a Darlington circuit. U1 is used as a voltage regulator, with VR1 the zener reference. Q4 and Q5 are used to limit the control line voltage to the oscillator. They are tuned on by S1 on the divider control. This switch has binary coded decimal outputs, and depends on the frequency selected by the first thumb-wheel switch. Either or both Q4 and Q5 may be turned on. When either is turned on, a voltage limit is developed across the precision resistors which are coupled to the control line. This voltage overrides the control voltage from the phase comparator and limits the oscillator range. This prevents the synthesizer from locking falsely on a harmonic.



PHASE COMPARATOR A1A3(S)

The phase comparator converts the difference between the phase of the variable counter and the reference generator to an error voltage. Note that the frequency of these two signals is the same, but they differ in phase. Q3 is a voltage regulator of the capacitor multiplier type. C9 and R13 are filters for the regulated 18 to 20 V d.c. input supply. VR1 is the zener diode which provides the reference voltage. C7 and C8 are bypass capacitors for VR1, with R11 and R12 the bias for Q3. C5, C6, and R9 are filters for the regulated output of Q3. R28 is a decoupling component to further filter the input voltage to the reference generator. R27 and VR2 establish the regulated +5V for the reference generator. Q1 is a switch for the square wave from the reference generator. R1, R2, and C1 differentiate the leading edge of the incoming square wave to cause a quick turn-on of Q1. This drives the ramp generator Q2. When Q1 conducts, it discharges C2 and C3, and pulls the base and emitter of Q2 toward ground. After Q1 turns off, C2, C3, R4, and R5 are used as an RC time constant to create a ramp. Since Q2 is an emitter follower, the output is bootstrapped back to the base to increase the ramp. R7 is used to linearize the ramp. R6 and R8 are bias resistors for Q2.

Q5 is a switch for the negative pulse from the divider control circuit which is differentiated by C10 and R15. R14 and R16 are bias resistors. C11 and R17 couple the leading edge of the signal to the gate of Q6 while also providing a high impedance. The ramp generator output is applied to the source of Q6 and is a varying d.c. voltage. When the sample pulse from the divider control is applied, Q6 conducts the d.c. level that is on the source at that particular instant, and this d.c. level is stored on C12. This level is held until the next sample pulse. Thus the circuit "samples" the d.c. level of the ramp, and "holds" it. This "hold" voltage is a continuous voltage that is proportional to the phase difference of the two input signals. During search mode (before phase lock occurs), CR1 or CR2 conduct because there is greater than 0.6 volt across them. After phase lock occurs, the voltage differential is low and **R25** provides isolation for any noise that might be present. U1 is a high input impedance operational amplifier which is used as a d.c. level shifter to provide the proper d.c. level for the voltage-tuned oscillator. It has almost unity gain, with R19 and R26 providing the nominal operating level. R21, C14, R22, C15, R23, C16, R24, and C18 form a multisection low-pass filter which is used to remove any undesired a.c. signal from the control voltage to the voltage-tuned oscillator. During search mode, most of the filter is bypassed by L1 and CR2 or CR3, which conduct when the voltage differential is greater than 0.6 volt.



EQUIPMENT MODIFICATIONS

ECP	520	CHAN	GES

CHANGE R2 FROM 1M TO 1.3M CHANGE E8 VOLTAGE +5.5 Vdc TO 5.8 Vdc ECP 648 CHANGE CHANGE U1 TO BE EITHER &PIN (507386-2) or 14-PIN (507386-1) AUD NOTE 3

ECP 470 CHANGES DELETE VR1 (1N754A) DELETE R7 (20 OHMS) DELETE R8 (1K) DELETE CR1 (2N2323)
SWITCHING REGULATOR A1A5(S)

This printed wiring board consists of an input filter, a power switch driver, an overvoltage shutdown circuit, and an output filter. The input filter consists of C1, C2, and L3. U1 is the switch driver, with R3 used as a short circuit protector. R4, R5, and R6 form a voltage divider string. L1 is an inductor which filters the d.c. pulses from the power switch. Operation consists of U1 being turned on by the feedback sensor after it drops to a sufficiently low value. It is an operational amplifier with its own internal reference diode. It operates as a switch and is either on or off. It drives an integrated circuit mounted on the back of the synthesizer which is a power switch. This switch conducts the unregulated d.c. for short pulses, operating at 40 kHz switching frequency.



Figure 11-20A. T0-5/T0-99 Installation in 14-Pin Dual Inline Package (DIP) Socket

Voltage regulator U1 in the synthesizer switching regulator (A1A5) is no longer manufactured in the 14-pin dual inline package. U1 may be replaced with either the 14-pin DIP or with the 8-pin T0-5 or T0-99 package that is electrically equivalent. Use one or the other; do not install both on the sme circuit card. Figure 11-20A illustrates how the 8-pin T0-5 or T0-99 is to be installed to replace the 14-pin DIP in case of failure of the 14-pin DIP.

11-39/11-40 (blank)



Figure 11-21. Mixer/Multiplier (UHF) A2 G1

MIXER/MULTIPLIER (UHF) A2 G1

The uhf mixer/multiplier module consists of an agc-controlled RF stage, a mixer stage, a local oscillator frequency quadrupler stage, a buffer amplifier stage, an amplifier stage, a feedback amplifier stage and a series regulating stage for gain control. The RF input from the antenna is directly coupled to a tap on L10. The input tuned circuit consists of L10 and variable capacitor C30 which is peaked at the incoming RF. The input RF signal is coupled through C31 to gate 1 of the dual gate field effect transistor RF stage Q7. The source of Q7 is supplied through R23 and R24 from the cathode of zener diode VR1.

The voltage at gate 2 of Q7 is developed by the voltage divider consisting of R28, VR2, and R27 and is supplied to gate 2 of Q7 through R21 and L18. The agc input is connected through R18 to common emitter agc amplifier Q6. The agc input is also connected through L15 and pin diode CR5 to voltage divider R38 and R39. As the agc voltage level increases with increasing RF signal level, the pin diode is driven into conduction and thus attenuates incoming signals and prevents Q7 and Q8 from being overdriven. As the agc voltage increases, Q6 is driven harder into conduction and reduces the voltage supplied to gate 2 of Q7 by shunting VR2 and R27 in the voltage divider that provides bias for gate 2 of Q7.

The output at the drain of Q7 is coupled through C49 to parallel tuned circuit L12 and C35. C35 is adjustable to peak the signal at the received RF. The signal is then coupled through C54 to gate 1 of the dual-gate field effect transistor mixer stage Q8. The quadrupled crystal oscillator frequency is applied to gate 2 of Q8 and the intermediate frequency of 20.6 MHz is produced at the drain of Q8. Variable capacitor C39 is adjusted for maximum IF signal output. Impedance matching for the output circuit of Q8 is provided by matching network C38, C39, L13, and C40. Temperature compensation is provided by R45 and thermistor RT1. The IF signal is also detected by CR4 and applied through R37 to the receiver front panel major test point MIXER OUT as a positive voltage level.

The output from the oscillator module is coupled through C1 to the base of quadrupler Q1. Bias for Q1 is supplied through R44 from the voltage divider R1 and R2. C12 is adjusted to peak the signal in the collector of Q1 at four times the frequency applied to the base. The quadrupled frequency is coupled through C16 to the emitter of common base buffer amplifier Q2. C11 is adjusted to peak the signal at the collector of Q2 at four times the oscillator frequency. The signal is coupled through C17 to the base of amplifier Q3. C27 is adjusted to peak the signal at the collector of Q3 at four times the oscillator frequency. The signal is coupled through C16 to gate 2 of Q8. The voltage at the collector of Q3 is also detected by CR1 and applied through potentiometer R17 to the base of feedback amplifier Q4. The collector voltage of Q4 in turn controls the base to emitter bias for series regulator Q5. Q2 operates between cutoff and saturation. Q5 controls the output of Q2 by controlling the d.c. supply voltage to Q2 and thus the operating point of Q2. The detected voltage from CR1 is also applied to the front panel major test point MULT.



Figure 11-22. Mixcr/Multiplier (UHF) A2 G2

MIXER/MULTIPLIER (UHF) A2 G2

The uhf mixer/multiplier module consists of an agc-controlled RF stage, a mixer stage, a local oscillator frequency quadrupler stage, a buffer amplifier stage, an amplifier stage, a feedback amplifier stage, and a series regulating stage for gain control. The RF input from the antenna is directly coupled to a tap on L10. The input tuned circuit consists of L10 and variable capacitor C30 which is peaked at the incoming RF. The input RF signal is coupled through C31 to gate 1 of the dual gate field effect transistor RF stage Q7. The source of Q7 is supplied through R23 from the cathode of zener diode VR1.

The voltage at gate 2 of Q7 is developed by the voltage divider consisting of R28, VR2, and R27 and is supplied to gate 2 of Q7 through R21 and L18. The agc input is divided by R18 and R19 and applied to the base of common emitter amplifier stage Q6. The agc input is also connected through L15 and pin diode CR5 to voltage divider R38 and R39. As the agc voltage level increases with increasing RF signal level, the pin diode is driven into conduction and thus attenuates incoming signals and prevents Q7 and Q8 from being overdriven. As the agc voltage increases, Q6 is driven harder into conduction and reduces the voltage supplied to gate 2 of Q7 by shunting VR2 and R27 in the voltage divider that provides bias for gate 2 of Q7.

The output at the drain of Q7 is coupled through C49 to parallel tuned circuit L12 and C35. C35 is adjustable to peak the signal at the received RF. The signal is then coupled through C54 to gate 1 of the dual-gate field effect transistor mixer stage Q8. The quadrupled crystal oscillator frequency is applied to gate 2 of Q8 and the intermediate frequency of 20.6 MHz is produced at the drain of Q8. Variable capacitor C39 is adjusted for maximum IF signal output. Impedance matching for the output circuit of Q8 is provided by matching network C38, C39, L13, and C40. Temperature compensation is provided by R45 and thermistor RT1. The IF signal is also detected by CR4 and applied through R37 to the receiver front panel major test point MIXER OUT as a positive voltage level.

The output from the oscillator module is coupled through C1 to the base of quadrupler Q1. Bias for Q1 is supplied through R44 from the voltage divider R1 and R2. C12 is adjusted to peak the signal in the collector of Q1 at four times the frequency applied to the base. The quadrupled frequency is coupled through C16 to the emitter of common base buffer amplifier Q2. C11 is adjusted to peak the signal at the collector of Q2 at four times the oscillator frequency. The signal is coupled through C17 to the base of amplifier Q3. C27 is adjusted to peak the signal at the collector of Q3 at four times the oscillator frequency. The signal is coupled through C16 to gate 2 of Q8. The voltage at the collector of Q3 is also detected by CR1 and applied through L9 and potentiometer R17 to the base of feedback amplifier Q4. The collector voltage of Q4 in turn controls the base to emitter bias for series regulator Q5. Q2 operates between cutoff and saturation. Q5 controls the output of Q2 by controlling the d.c. supply voltage to Q2 and thus the operating point of Q2. The detected voltage from CR1 is also applied to the front panel major test point MULT.

11-47/11-48 (blank)



8004351G1 CIRCUIT CARD ASSY.

Figure 11-23. Mixer/Multiplier (VHF) A2 G1

MIXER/MULTIPLIER (VHF) A2 G1

The vhf mixer/multiplier module consists of a temperature-compensated and agc-controlled RF stage, a mixer stage, a local oscillator frequency doubler stage, and a buffer amplifier with a temperature compensated feedback stage. Optimum gain for the module is 12 to 14 dB. The RF input from the antenna is coupled through C36 and C37 to a tap on L1. Resonance at the received frequency is achieved by adjusting variable capacitor C1. The signal from a tap on L1 is coupled through C2 to gate 1 of dual-gate field effect transistor Q1. The source of Q1 is supplied through R7 and R8 from the cathode of zener diode VR1. The +3.3 volts established by the diode, is used to raise the source of Q1 sufficiently above ground so that the gates may be negatively biased relative to the source.

This voltage at gate 2 of Q1 is developed from the agc input to the module. The agc input is divided by R1 and R2 and applied to the base of common-emitter amplifier stage Q3. The agc input is also connected through L15 and pin diode CR4 to the voltage divider R29 and R30. As the agc voltage level increases with increasing RF signal level, the pin diode is driven into conduction and thus attenuates incoming signals and prevents Q1 and Q2 from being overdriven. The collector of Q3 becomes less positive as the input agc level becomes more positive. This voltage is a bias voltage direct coupled to gate 2 of Q1 after being level changed by zener diode VR2 allowing the agc input to control the level of the RF signal through Q1. The output at the drain of Q1 is coupled through C7 to parallel tuned circuit L3 and C9. C9 is adjustable to peak up the signal at the received RF frequency. The signal is then coupled through C10 to gate 1 of the dual-gate field effect transistor mixer stage Q2. The doubled crystal oscillator frequency is applied to gate 2 of Q2 and the intermediate frequency of 20.6 MHz is produced at the drain of Q2. Variable capacitor C41 is adjusted for maximum output at the IF signal. Impedance matching for the output circuit is provided by matching network L5, C18, C41, and C42. Temperature compensation is provided by thermistor RT3 and R36. The IF signal is also detected by CR1 and applied through R15 to the receiver front panel major test point MIXER OUT as a positive voltage level.

The output from the oscillator module is coupled through C21 to the base of doubler stage Q4. This signal is 0.6 to 1.0 volt rms. Approximately a +0.6 volt bias voltage is applied through R31 to the base of Q4. C24 is adjusted to peak up the signal in the collector of Q4 at twice the signal frequency impressed upon the base. This doubled frequency is induced from L9 into L10 and coupled through C25 to the emitter of buffer amplifier stage Q5. A feedback loop from Q6 establishes the voltage level on the base of Q5 thereby controlling the emitter-base bias of Q5 stabilizing its output. C29 is adjustable to resonate at the frequency produced by the preceding doubler stage. This output is coupled through C33 and C11 to gate 2 of mixer stage Q2 as previously discussed. The output is also detected by CR3 and applied through a low pass pi filter and R27 to the base of Q6. R26 provides level control by controlling the feedback voltage to Q5; temperature compensation is provided by RT2. The detected and filtered output is also applied through R28 to the receiver front panel MULT test point.



MIXER/MULTIPLIER (VHF) A2 G2

The vhf mixer/multiplier module consists of a temperature-compensated and agc-controlled RF stage, a mixer stage, a local oscillator frequency doubler stage, and a buffer amplifier with a temperature compensated feedback stage. Optimum gain for the module is 12 to 14 dB. The RF input from the antenna is coupled through C36 and C37 to a tap on L1. Resonance at the received frequency is achieved by adjusting variable capacitor C1. The signal from a tap on L1 is coupled through C2 to gate 1 of dualgate field effect transistor Q1. The source of Q1 is supplied through R7 from the cathode of zener diode VR1. The +3.3 volts established by the diode, is used to raise the source of Q1 sufficiently above ground so that the gates may be negatively biased relative to the source.

The voltage at gate 2 of Q1 is developed from the agc input to the module. The agc input is divided by R1 and R2 and applied to the base of common emitter amplifier stage Q3. The agc input is also connected through L15 and pin diode CR4 to the voltage divider R29 and R30. As the agc voltage level increases with increasing RF signal level, the pin diode is driven into conduction and thus attenuates incoming signals and prevents Q1 and Q2 from being overdriven. The collector of Q3 becomes less positive as the input age level becomes more positive. This voltage is a bias voltage direct coupled to gate 2 of Q1 after being changed in level by zener diode VR2 allowing the agc input to control the level of the RF signal through Q1. The output at the drain of Q1 is coupled through R38 and C7 to parallel tuned circuit L3 and C9. R38 is a parasitic suppression resistor. C9 is adjustable to peak up the signal at the received RF frequency. The signal is then coupled through C10 to gate 1 of the dual-gate field effect transistor mixer stage Q2. The doubled crystal oscillator frequency is applied to gate 2 of Q2 and the intermediate frequency of 20.6 MHz is produced at the drain of Q2. Variable capacitor C41 is adjusted for maximum output at the IF signal. Impedance matching for the output circuit is provided by matching network L5, C18, C41, and C42. Temperature compensation is provided by thermistor RT3 and R36. The IF signal is also detected by CR1 and applied through R15 to the receiver front panel major test point MIXER OUT as a positive voltage level.

The output from the oscillator module is coupled through C21 to the base of doubler stage Q4. This signal is 0.6 to 1.0 volt rms. Approximately a +0.6 volt bias voltage is applied through R31 to the base of Q4. C24 is adjusted to peak up the signal in the collector of Q4 at twice the signal frequency impressed upon the base. This doubled frequency is induced from L9 into L10 and coupled through C25 to the emitter of buffer amplifier stage Q5. A feedback loop from Q6 establishes the voltage level on the base of Q5 thereby controlling the emitter-base bias of Q5 stabilizing its output. C29 is adjustable to resonate at the frequency produced by the preceding doubler stage. This output is coupled through C33 and C11 to gate 2 of mixer stage Q2 as previously discussed. The output is also detected by CR3 and applied through a low pass pi filter and R27 to the base of Q6. R26 provides level control by controlling the feedback voltage to Q5; temperature compensation is provided by RT2. The detected and filtered output is also applied through R28 to the receiver front panel MULT test point.



Figure 11-25. Preamplifier, AF/AGC-Squelch A3

	TEST POIN	TVOLTAGES			
	ALL POTE	NTIOMETERS FUI SQUELCH	LL COUNTER CLOCKW	ISE	
		OFF	ON		
	TP1	12.0 ± 1.0VDC	1.5 +0.2VDC		
	192	4.5 ±0.5VDC	4.3 ±0.2VDC 4.5 ±0.5VDC		
	TP3 TP4	4.5 ±0.5VDC 3.4 ±0.5VDC	3.4 ±0.5VDC		
	TP5	12.0 + 1.0VDC	12.0 ± 1.0VDC		
	TP6 TP7	9.0 ±0.5VDC 9.5 ±0.5VDC	8.9 ±0.5VDC 9.5 ±0.5VDC		
	TP8	7.5 ±0.5VDC	7.5 ±0.5VDC		
	TP9	9.0 ± 0.5VDC	9.0 ±0.5VDC 9.5 ±0.5VDC		
	TP10	9.5 ±0.5VDC			
	MP1	2.5 ±0.2VDC	2.5 ±0.2VDC		
	MP2	4.0 + 0.5VDC	4.0 ±0.5VDC		
	MP3 MP4	0.6 ±0.2VDC 12.0 ±1.0VDC	0.6 ±0.2VDC 12.0 ± 1.0VDC		
-	MP5	5.0 + 0.5VDC	5.0 ±0.5VDC		
3>	MP6	3.0 ±0.5VDC 5.4 ±0.2VDC	1.8 ±0.5VDC 5.4 ±0.2VDC		
	MP7 MP8	17.0 ± 1.0VDC	0.65 ±0.05VDC		
н	MP9	8.5 ±0.5VDC	0.32 ±0.05VDC		
	MP10 MP11	2.7 ±0.2VDC 9.0 ±0.5VDC	2.7 ±0.2VDC 9.0 ±0.5VDC		
	MP12	12.0 + 1.0VDC	12.0 ± 1.0VDC		
	MP13 MP14	8.5 + 0.3VDC 9.0 + 0.5VDC	0.32 ±0.05VDC 8.9 ±0.5VDC		
	MP14 MP15	9.0 ±0.5VDC	8.9 ±0.5VDC		
	MP16	9.0 + 0.5VDC	8.9 ±0.5VDC		
	MP17 MP18	8.5 ±0.2VDC 10.3 ±0.5VDC	8.5 ±0.5VDC 10.3 ±0.5VDC		
	MP19	1.75 + 0.1VDC	1.75 ±0.1VDC		
POINT					
	NOTES				
	UNL	ESS OTHERWISE	SPECIFIED	EQUIPMEN	T MODIFICATIONS
		RESISTANCE VA	LUES ARE IN OHMS,	CIB FROM	0.01 TO 0.022
		CAPACITANCE	ALUES ARE IN		
		ROFARADS, : 103			
	3 THE	SE LEVELS ARE I	DEPENDENT		
		1			1
			R67 392K ≰R69	R71	
		1	1% \$470	47	1
18	C19	C20	1/ 4W	1	1
.022 00V		00V 0.0 . 100V	013 2N2222A	1	
(() 2N222	24	1
19 🛨	\$ R65	\$ R66 7	R68 392K	14	15 PINS
14148I	40.2K	40.2K	1% (1371143
•	1 BW	1/8W	1/000 R70	\mathbf{i}	AF PREAMP OUTPUT
			₹100K	E1	6
			+		Î.
					i
		R72 1K		EI	AF PREAMP OUTPUT
		+	— —	E1	7 7
			C21 2.2		
			2.2		
					-
					1
					•

PREAMPLIFIER, AF/AGC-SQUELCĤ A3

The audio input comes into P1 through pin 12 and is coupled through C4 to limiter diodes CR3, CR4, and CR8. This limiter clips noise and transients that occur on the audio input. The audio signal is then coupled through the voltage divider (R31 and R32), through capacitor C5 to the compression control FET Q7. The audio signal is fed through Q7, through capacitor C6 to the audio amplifier, Q8. Q8 amplifies the audio signal, coupling the amplified signal through C9 to amplifier Q10. Q10 further amplifies the audio signal and couples the output to a floating limiter consisting of CR6, CR7, R55, C12, and C13. This floating limiter provides limiting action around the d.c. bias level, and further limiting of unwanted noise pulses that occur in the audio passband. At this point in the circuit, the audio is compressed and maintains a near constant peak-to-peak signal level, and the floating limiter limits at levels just above and below the compression peakto-peak audio level. The signal is then coupled through squelch control FET Q11 (described later) to emitter follower Q12. The output from Q12 is then coupled through the low-pass filter amplifier circuit consisting of R60, C15, R61, C17, R62, and C16, to operational amplifier U2. This low-pass filter and the high-pass filter (C18, C19, R65, R66, C20, R67, R68, Q13, Q14, R69, R70, and R71) maintain a receiver band pass of 300 to 3000 Hz within +1 to -2 dB of the reference frequency of 1000 Hz. The band pass of this filter rolls off the low end to at least 10 dB down at 100 Hz and at least 10 dB down at 10 kHz.

The audio output from the preamplifier path is coupled back to an amplifier consisting of transistor Q9 and associated biasing components. This stage amplifies the audio and detects and provides a d.c. bias to the compression FET Q7. Adjustment of the compression level is accomplished by an adjustment of R41 potentiometer which controls the amount of compression and the signal level output. This feedback compression circuit maintains a constant audio level output with varying audio input signals. The audio output from this module is coupled to the gain control on the front panel; consequently all compression takes place before the main audio gain control. Thus, compression is obtained at any audio signal level output. The compression detection takes place in diode CR5, and any ripple is filtered out by capacitor C7. This provides d.c. bias, proportional to the audio level, to the FET gate through resistors R73 and R34.

FET Q11 provides a series squelch switching action that turns the audio output on and off as a function of the agc amplifier. When the gate control voltage to Q11 is biased to a turn-off point, no audio signals pass through Q11. The source and the drain voltage potentials are nearly the same, thus providing no d.c. level shift when the transistor is turned off. When the transistor is turned on, the audio signal proceeds through Q11 with very little attenuation. It is the equipotential source and drain voltages that provide the quiet switching action of this squelch switch.

The automatic gain control amplifier consists of a differential amplifier, an emitter follower amplifier stage, and two additional amplifier stages. The detected carrier is coupled through R30 to the base of differential amplifier stage Q1. This transistor shares an emitter load network with Q2 consisting of R2, R3, and R5. The operating level of Q2 is adjusted by R7. The voltage at the junction of R6 and R9 is regulated by zener diode VR1. R11, RT1, and R10 are for temperature compensation. The adjustable voltage applied to the base of Q2 is established by the voltage divider composed of R6, R7, and R8. Direct coupling is used throughout the agc amplifier. The output from the differential amplifier, the collector of Q2, is applied to the base of emitter follower g3 output is applied to the base of Q4. The collector of Q4 is connected directly to the base of Q5. The agc output is taken from the collector of Q5. This output is also applied through R18 to the receiver front panel major test point AGC, to the squelch circuit (located in this same module) via R19, and the receiver front panel squelch control potentiometer.

The squelch circuit is essentially an electronic switch which turns on the preamplifier squelch FET when the detected signal reaches a certain level and turns off the FET when the detected signal is reduced to a certain level. With the receiver front panel squelch switch in the ON position, the agc voltage is applied across R19 and the front panel squelch adjust (R1 and R28). The wiper of front panel control R1 is directly coupled through resistor R23 to pin 3 of the operational amplifier U1. If the detected RF level increases, the output from operational amplifier pin 6 goes positive and turns on squelch FET Q11 in the preamplifier circuity. If the detector RF level decreases (as indicated by a decrease of the agc level) to the squelch level, the output from operational amplifier U1 decreases, thus turning off squelch FET Q11 in the preamplifier circuity. Complete and rapid switching is insured by the feedback path resistor R22 around the operational amplifier U1. Diode CR2 provides fast decay of squelch switch filtering capacitor C14 when the squelch switch turns off. When the receiver unsquelches, resistor R24 provides a short time constant action to charge C14 so that small squelch delay occurs to provide inhibiting of unwanted transients at the time of initial detection of input signals. Q6 provides a monitor output drive and serves as an isolation transistor for the squelch test point.

11-59/11-60 (blank)



Figure 11-26. Audio Frequency Amplifier A4

MEASUREMENT POINT VOLTAGES

MP1	2.7 ±0.6VDC
MP2	6.5 ±1.2VDC
MP3	16 ±2VDC
MP4	9.3 ±2VDC
MP5	0.55 + 0.14VDC
MP6	0.55 ±0.14VDC
MP7	5.0 ± 1.0VDC
MP8	4.0 ±0.5VDC
MP9	12.0 ± 1.0VDC
MP10	0.25 ±0.1VDC
MP11	0.25 ±0.1VDC

TEST POINT VOLTAGES

TP1	1.0 V ±0.3 VDC
TP2	7.5 V ±0.5 VDC
TP3	1 V <u>+</u> 0.3 VDC
TP4	1 V ±0.2 VDC
TP5	8.5 V ±1 VDC
TP6	1 V ± 0. 2 VDC

NOTES:

UNLESS OTHERWISE SPECIFIED:

1. RESISTANCE VALUES ARE IN OHMS, ±5%, ¼ W. 2. CAPACITANCE VALUES ARE IN MICROFARADS, ±10%, 500V. 3. DIODES ARE 1N914. 4. TRANSISTORS ARE 2N1613. 5. ALL VOLTAGE MEASUREMENTS TAKEN WITH A HIGH INPUT IMPEDANCE METER (HP427 OR EQUIVALENT).

AUDIO FREQUENCY AMPLIFIER A4

The audio frequency amplifier consists of two separate audio amplifier systems. The main audio amplifier receives an input signal controlled by the AUDIO MAIN ADJ screwdriver adjustment on the receiver front panel, and supplies an output to a connector on the receiver rear apron for remote speaker operation. The secondary audio amplifier receives an input controlled by the PHONE ADJ control on the receiver front panel, and supplies an output to the PHONE OUTPUT jack on the receiver front panel.

The main audio amplifier consists of a common-emitter amplifier stage, a phase-splitter stage, a pushpull driver stage, a push-pull output stage, and an output transformer. The input audio signal is coupled through C1 and R16 to the base of common-emitter amplifier stage Q5. Degenerative feedback to this stage is employed to provide adequate regulation of the output signal voltage. This negative feedback signal is derived from output stage Q3 and is also coupled to the base of Q5 via R24 and C11. The signal from the collector of Q5 is coupled through C2 to the base of phase splitter Q6. The phase splitter provides signals of equal magnitude and opposite polarity to the output driver stage consisting of Q1 and Q2. Temperature compensation of bias for the driver stage is provided by CR2 and CR3.

The output signal from the emitters of driver stage Q1 and Q2 is direct coupled to the push-pull output stage at the base of Q3 and Q4. The collectors of Q3 and Q4 are connected to the primary of output transformer T1. The center tapped secondary of T1 is connected to a rear apron connector on the receiver. Signal voltage across T1 is limited to approximately 43 volts peak-to-peak maximum by the action of zener diodes VR1 and VR2. A compression output to the audio preamplifier/agc squelch module is provided from the collector of Q3. The signal from the collector of Q4 is divided by R46 and R47 and coupled through C24 to the receiver front panel major test point MAIN AF.

The secondary audio amplifier consists of a common-emitter amplifier stage, a phase splitter, a pushpull output stage and an output transformer. The input audio signal is coupled through R25 and C13 to the base of common-emitter amplifier stage Q7. Degenerative feedback from the collector of Q9 is also coupled to the base of Q7 via C14 and R26. The signal is coupled from the collector of Q7 through C19 to the base of phase splitter stage Q8. High frequencies are attenuated through the action of C20 and R37. Q8 provides signals of equal magnitude and opposite polarity to the push-pull output stage consisting of Q9 and Q10. The push-pull output stage drives the output transformer T2. The voltage across the primary of T2 is limited to a maximum of approximately 43 volts peak-to-peak by the action of zener diodes VR3 and VR4.

Surge protectors are provided to protect the audio amplifier output circuits from \pm 1000 volts peak input pulses applied to each audio output. Protection for the main audio amplifier output is provided by surge protectors E1 and E2. These are mounted on terminal board TB1 adjacent to the rear apron connector J2. Protection for the secondary audio amplifier is provided by E8 mounted on the back of the receiver front panel PHONE OUTPUT jack.

NOTES:

UNLESS OTHERWISE SPECIFIED:

11.5 ± 1VDC

TP2

VR1 TP2 P1 **1.** ALL RESISTANCE VALUES ARE IN OHMS L5 1N753A O 5.6 + 5%, 1/4 WATT. +18∨ 3 ← 2. ALL CAPACITANCE VALUES ARE IN E3 木 C7 PICOFARADS + 20%, 500 VOLTS. **C**8 47 UF ⊥ 2200 - 3. ALL INDUCTANCE VALUES ARE IN MICROHENRIES. <u>+</u> 10% 4. ALL VOLTAGE MEASUREMENTS TAKEN 20V WITH A HIGH IMPEDANCE METER (HP427) OR EQUIVALENT. ΜP **P1** GND 1 PANEL L3 L4 E4 E5 Ŧ **→**5 TEST 5.6 0.56 C6 POINT 1000 C5 (NOISE LIM) R9 C11 1000V 2200 100 1000 **R8** 기 Ŧ 1000V 2200 MP *** 1 **R1** R3 R10 C10 1000 CR1 5.6K 10 68 L2 L1 5082-8906(HP) <u>+5%</u> P2 E1 5.6 J1 5.6 E6 01 OUTPUT INPUT) 15 I۲ 2N5109 **R6 C4** E7 • E2 47 2200 -0 TP1 C2 R2 15-60 1.5K **R7** R5 R4 5 200V 120 39 120 **MEASUREMENT/TEST POINT VOLTAGES** MP1 2 ±0.5VDC 0.46 ± 0.1VDC MP2 TP1 1.3 + 0.5 VDC

Figure 11-27. Buffer Amplifier A5

BUFFER AMPLIFIER A5

The function of the buffer amplifier is to provide a 50-ohm source impedance for the crystal filter and approximately a 50-ohm load to the mixer/multiplier module. The operating frequency is 20.6 MHz. The amplifier gain is 0 ± 1 dB and its 3-dB bandwidth is about 4 MHz. The tunable capacitance (C2) is adjusted for maximum gain at 20.6 MHz when J1 is fed from a 50-ohm generator and P2 is loaded with 50 ohms. The +18 V d.c. supplied to the module is regulated to about 12 V d.c. by VR1, a 6.2 volt zener diode. L5 prevents RF from leaving the module on the 18 V d.c. line and C7 and C8 provide a low a.c. impedance to keep the signal off the 12 V d.c. line.

L1, L2, and C2 are the input matching network. R1 and R2 bias Q1 so that its collector current is about 35 mA. L3 and C5 prevent any residual RF that may be on the 12 V d.c. line from appearing at the base of Q1. Both R4 and the series combination of R3 and C6 provide degenerative feedback for the amplifier, making it stable, and allowing interchangeability of transistors without gain change. L4 is the collector load. C10 accomplishes impedance stepdown from the collector impedance to the 50ohm impedance of the 7.5 dB pad (R5, R6, and R7). R10 suppresses any tendency toward high frequency oscillations. When the signal at the output (P2) is large enough (greater than 0.5 V rms), CR1 rectifies a portion of the signal and C11 filters it to give a d.c. indication on the condition of the module at the NOISE LIM test point at the front panel of the receiver.



Figure 11-28. Electrical Noise Limiter A5

NOTES	TEST POINT VI	DLTAGES	MEASURING	POINT VOLTAGES	MP16 MP17	11.4 +).4VDC 12.0 +).4VDC
UNLESS OTHERWISE SPECIFIED 1 RESISTANCE VALUES ARE IN OHMS ± 5%, 1/4W. 2 CAPACITANCE VALUES ARE IN PICOFARADS ± 10%, 1000V. 3 INDUCTANCE VALUES ARE IN MICROHENRIES ± 10%, 4 ALL VOLTAGE MEASUREMENTS TAKEN WITH A HIGH INPUT IMPED ANCE METER (HP427 OR EQUIVALENT)	191 (WITH NOISE) 192 193 194 195 196 197 198 199 199 199 1910 1911 1912	>12USEC BLANK 12V ±1VDC 10V ±2VDC 2 5V ±0 5VDC 0 1.5V ±0.5VDC 2V ±0 5VDC 1V ±0.2VDC 10V ±2VDC 11V ±1VDC 5V ±0.2VDC 1V ±0.2VDC	MP1 MP2 MP3 MP4 TO MP5 MP5 MP5 MP7 MP10 MP11 MP11 MP13 MP14 MP15	2 4 ± 0.2VDC 1.8 ± 0.2VDC 11.4 ± 0.4VDC 1.9 ± 0.5 0HMS 4.25 ± 0.75VDC 6.25 ± 0.75VDC 6.25 ± 0.75VDC 6.0 ± 0.3VDC 1.3 ± 0.3VDC 1.4 ± 0.2VDC 0.8 TO 2.5VDC 3.8 ± 0.2VDC 3.2 ± 0.2VDC	MP18 MP19 MP20 MP21 MP22 MP23 MP24 MP25 MP25 MP25 MP26 MP29 MP29 MP30 E2 E7	0.4 ±0 1VDC 0.5 ±0 1VDC 2.9 ±0 1VDC 1.8 ±0 1VDC 4.2 ±0 2VDC 4.0 ±1.5VDC 0.5 ±0 6VDC 0.5 ±0 6VDC 0.5 ±0.1VDC 1.0 ±0.2VDC 0.5 ±0 2VDC 5 ±0 2VDC 5 ±0 30VDC 1.5 ±0.2VDC 1.0 ±0.5VDC

Z3

A PULSE DETECTOR B AGC CUNTROL C PULSE AMPLIFIER

ELECTRICAL NOISE LIMITER A5

The signal applied to noise limiter module input J1 flows through an amplifier, a 0.2- μ s delay line, and a gating circuit to output P2 with unity gain. The same signal applied to the input also flows into a circuit which establishes a d.c. voltage directly proportional to the amplitude of the intermediate frequency signal. If a pulse of noise occurs which is from 20 to 30 dB higher than the signal voltage, the gate is closed and the output signal is momentarily cut off. A pulse stretching effect occurs in this second loop so that the output signal is gated off for a slightly longer time than that occupied by the noise pulse. These signal blank out periods are of such short duration that they cause no adverse effect on the audio signal at the receiver output.

The IF input of J1 is applied through an impedance matching network to the base of amplifier stage Q1. C2 and C5 are adjustable to obtain the best impedance match between the 50-ohm input J1 and the amplifier input. Amplifier Q1 boosts the signal level to compensate for signal degradation in delay line DL1 and following circuitry, thereby maintaining a net gain of 1 for the module. The signal is coupled from the collector of Q1 to the 0.2- μ s delay line by C8 and C9. C8 and C10 are adjustable for an impedance match with the 50-ohm delay line input impedance. The output of DL1 is applied through a pin diode gate made up of CR3 and CR4 to module output connector P2. Normally, with no noise pulse present, CR3 and CR4 are forward biased presenting minimum impedance to signal flow to the module output connector P2.

The signal input at J1 is also applied to the gate control loop consisting of an IF amplifier, a detector, an agc feedback loop, a pulse amplifier, and a gate driver. Z1 and Z2 are integrated-circuit IF amplifiers. These amplifiers are broadband tuned as a result of discrete components external to the integrated circuits. Z1 receives an agc input at pin 2. Amplifier stage Q5 is tuned to the IF of 20.6 MHz by C38. The collector of Q5 is coupled to the input of integrated circuit Z3 at pin 9. Z3 contains a detector, an agc output, and a pulse amplifier. The agc level is adjusted by R44 and is fed back from Z3 pin 5 to Z1 pin 2. Temperature compensation is provided by CR6, CR7, and CR10.

The detected signal, along with any noise that might be present, is clamped above ground level through the action of CR8 and applied to the base of emitter follower Q7. The signal from the emitter of Q7 is then applied through R63 and R64 to the base of Q10. However, the signal at the junction of R63 and R64 is clamped below a variable voltage level dependent upon the average peak signal. The agc from Z3 pin 5 is also applied through R72 to the base of Q6 allowing C46 to charge up to a value representing the level positive excursion of the detected signal. The base of Q10 is clamped below that level through the action of CR9. When a noise spike occurs extending more positive then the average signal level, it passes through emitter follower Q10 and is amplified by pulse amplifier Q8 and Q9. The noise spike is then coupled through C12 to the base of Q2. The action of CR1, R12, C15, R13, and C14 stretches and couples the pulse to the base of Q3. Q3 cuts off for the duration of the pulse and Q4 goes into conduction, applying +12 volts to the cathode of pin diode gate CR3 via R20 and L5. CR3 and CR4 are then backbiased for a time slightly longer than the duration of the noise pulse (+6 volts is applied to the anode of CR4 via R27 and L6) and the noise pulse is effectively removed from the receiver output.

At the end of the noise blanking pulse, Q3 resumes normal conduction and Q4 is cut off. This effectively connects the cathode of pin diode gate CR3 to ground via L5, R20, CR2, Q3, and R16, thus supplying forward bias to the pin diodes opening the gate. The +18 volts on P1-3 is decreased to +6 volts and +12 volts for use within the noise limiter module. The +6 volts is supplied by the regulator circuit consisting of R28, VR1, C26, and R29, and +12 volts is supplied by the regulator circuit consisting of Q11, R33, R34, VR2, and C49. The module signal output is also detected by diode CR5 and applied to receiver front panel major test point NOISE LIM.



Figure 11-29. IF Amplifier and Detector A6

TEST POINT VOLTAGES

TP1	2V <u>+</u> 0.5VDC
TP2	8V ± 1VDC
трз	8V ±1VDC
TP4	11V ± 1VDC

MEASURING POINT VOLTAGES

MP1 2.73 ±0.25VDC MP2 7.75 + 1.25VDC MP3 8 + 1VUC MP4 17 + 1VDC MP5 8.5 + 1VDC MP6 17 + 1VDC MP7 15.5 + 1VDC M98 9.5 ± 1VDC MH9 8.5 + 1VDC MP10 17.5 + 1VDC MP11 3+0.5VDC MP12 3+0.5VDC **MP13** 9 + 1VDC MP14 2 ±0.5VDC **MP15** 1.5 <u>+</u>0.5VDC E2 18 + 0.5VDC E6 11.25 ±1.25VDC E11 11 ± 1.5VDC E12 3 ±0.5VDC

> EQUIPMENT MODIFICATIONS ECP 474 CHANGE R3 FROM 2K TO 1.8K

ECP 536 CHANGE C1 FROM 47pF TO 22pF L1 FROM 0.47 H TO 0.56 H

ECP 568 CHANGE C43 FROM .022 TO .0022

11-73

IF AMPLIFIER AND DETECTOR A6

The intermediate frequency amplifier consists of four cascaded common-emitter IF stages followed by a detector and a low-gain IF stage base driven by the fourth stage. The low gain IF stage Q5 is an isolation amplifier whose output is coupled through J2 to the 50-ohm output connector J10 on the receiver rear panel. Detector Q6 is biased to perform the detection function and provide an audio signal to the audio preamplifier agc/squelch module. The detector also drives wideband audio amplifier Q7 and associated circuit components. The first amplifier, Q1, is a common-emitter configuration driven by the input IF signal through a matching network consisting of C1, C2, C3, and L1. C2 and C3 are provided to adjust the input impedance of the first stage to 50 ohms. The gain of this stage is controlled in a forward agc mode through the base bias resistor R2. The agc voltage controls the base drive through L2 and CR1. R1 and CR2 provide a fixed current to the bias network to maintain a high gain in the transistor in the absence of agc voltage.

The second and third stages, Q2 and Q3, are identical common-emitter stages driven in cascade by the first stage. The gain of each stage is controlled in a reverse agc mode by the injection of an agc voltage to the emitters of the transistors. The agc voltage is applied to the emitter of Q2 through R12, L9, and CR3. The agc voltage is applied to the emitter of Q3 through R15, L10, and CR4. The fourth stage, Q4, is a common-emitter stage, having no automatic gain control, which drives both the detector and the 50-ohm output isolation amplifier. Isolation amplifier Q5 is a low gain common-emitter stage which drives the 50-ohm output connector through a matching "T" network composed of R23, R24, and R25. The detector stage, Q6, uses its base-emitter junction to rectify the IF signal. C38, C43, and R37 filter out IF signal components and apply the filtered audio to the output connector. C39 couples the audio signal to the wideband audio amplifier which uses Q7 in a common-emitter output stage. The wideband amplifier has a 25-kHz passband.







Figure 11-30. Power Supply PS1

POWER SUPPLY PS1

The power supply is designed to operate from either a.c. or d.c. voltages. Jumpers are provided on terminal board TB1 to allow the power supply to operate at any one of the following primary voltages: 105, 120, 210, or 240 V a.c. $\pm 10\%$. Usable frquency for primary a.c. power is 47 to 420 Hz. In case of a.c. power failure, primary power is supplied to the power supply from an external battery (when available). With the supply operating on a.c., voltage is applied to the primary of transformer T1 via TB1. The secondary of T1 connects to the bridge rectifier (CR1, CR2, CR3, and CR4). An unregulated output of approximately +30 volts is provided at the junction of CR1 and CR2 for use as crystal oven heater power for the oscillator module. This same output flows through R2 and is reduced to +18 volts $\pm 0.5\%$ by series-pass transistor Q3 to supply the regulated voltage required by the receiver.

Q6 and Q7 form a differential amplifier driving emitter resistor R15. The regulator output voltage is applied across voltage divider R16, R17, and R18. A sample of the output from R17 is applied to the base of Q7. The level of the output voltage may be set by adjusting R17. A reference voltage established by zener diode VR2 is applied to the base of Q6 which is the other differential amplifier input. The output of the collector of Q7 is directly coupled to the base of common-emitter amplifier stage Q5. The voltage at the emitter of Q5 is held at a constant value by R11 and R24. A second input to the base of Q5 is applied by the short-circuit protection circuit via CR5. When the supply is operating with no short circuit present, CR5 will be back biased, effectively disconnecting the short-circuit protection input from the base of Q5.

The output of amplifier stage Q5, at the junction of resistors R9 and R6, is direct coupled to the base of common-emitter amplifier stage Q2. The collector of Q2 is direct coupled to the base of series-pass transistor Q3. The amplitude and polarity of this signal is such that a regulated +18 volts is produced at the emitter of Q3. Special circuitry is necessary to facilitate the start-up of the regulator. When power is turned on, capacitor C3 is charged up through resistor R7. The junction of R7 and C3 is connected to the base of Q5 through R8. When the voltage applied to the base of Q5 becomes positive enough, it overcomes the positive emitter voltage established by R24, and Q5 begins to conduct through R9 and R6. Current through R6 causes Q2 to start conduction which, in turn, allows conduction through series pass transistor Q3. When sufficient current flows on the regulated +18 volt line, the normal regulator takes control and the output is maintained at +18 volts. The relatively large value of R8 sufficiently isolates the start-up circuit to allow Q5 to be controlled by differential amplifier Q6 and Q7 when these transistors receive adequate operating voltage.

The battery is charged by a 300 mA nominal constant-current source when the power supply is operating from a.c. The battery charge path is from the junction of CR1 and CR2 through R22 and R23, Q8, and CR9 to the battery bus. Q8 is the series-pass transistor in the charging circuit. A constant voltage is applied to the base of Q8. This constant voltage is established by the voltage dropped across forward-biased diode string CR6, CR7, and CR8 (approximately 2 volts is dropped across the diodes). The charging current through emitter resistors R22 and R23 determines the emitter-base bias in Q8 and maintains the 300 mA nominal trickle charge rate. Reverse battery polarity protection is provided by stage Q9. With proper battery polarity, Q9 is in the cut-off region. However, if the battery is connected backward, a negative voltage will be applied to the base of Q9 causing heavy conduction. This eliminates the 2 volts dropped across diodes CR6, CR7, and CR8, and applies a back emitter-base bias to series pass transistor Q8. Transistor Q8 is then driven into the cut-off region and the battery charge path is interrupted.

When a short circuit occurs, a heavy current tends to flow through R2 and the series pass transistor Q3. An increase in current flow also occurs in R1 and R3. A forward emitter-base bias for Q1 is developed across R1 and Q1 starts to conduct. This applies forward bias to the emitter-base junction of Q4 which begins to conduct through R5. The collector of Q4 is connected through CR5 to the base of Q5 driving it into cutoff. Q5 is an amplifier stage in the regulator circuitry discussed in a previous paragraph. As a result of the regulator action, series pass transistor Q3 is cut off, removing the power supply regulated output from the receiver modules. C2 prevents extraneous activation of the short-circuit protection as a result of momentary changes in load. The short-circuit protection circuit is latching and once triggered by an overload, the regulated output is not reapplied until the receiver is turned off and then on again. Once an overload has occurred, current flows through Q4, R5, and R1. Current through R1 holds Q1 conducting which, in turn, maintains a forward bias on Q4 and holds it in conduction until primary power has been removed from the power supply.

In case of a.c. power failure, primary power will be supplied from the battery (when available). Current flow will be from the battery bus through isolation diode CR10, R2, and series pass transistor Q3 to all receiver modules requiring regulated voltage. The same regulator circuit is used regardless of whether using an a.c. or a d.c. power source. AF P 6500.1 CHG 413 Chap 391 1/18/90 TI 6620.2A



Figure 11-31. VHF Receiver Functional Blocked Diagram



11-79/11-80 (blank)

AF P 6500.1 CHG 418 Chap 391 TI 6620.2A 10/9/90 (Reprinted for clarity)

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Figure 11-34. UHF Receiver Functional Blocked Diagram Text

11-83/11-84 (blank)

PART OF AN/GRR-23 OR AN/GRR-24



Figure 11-35. Oscillator-Synthesizer Functional Blocked Diagram



HARDAR P.

PART OF AN/GRR-23 OR AN/GRR-24



11-87/11-88 (blank)

TI 6620.2A

AF P 6500.1 CHG 413 Chap 391 1/18/90 **TI 6620.2A**



Figure 11-37. VHF Receiver Blocked Schematic Diagram



11-91/11-92 (blar.k)



Figure 11-39. UHF Receiver Blocked Schematic Diagram



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11-95/11-96 (blank)

AF P 6500.1 CHG



Figure 11-41. Oscillator-Synthesizer Blocked Schematic Diagram

TI 6620.2A



AF P 6500.1 CH: 361 Chap 356 1/28/83